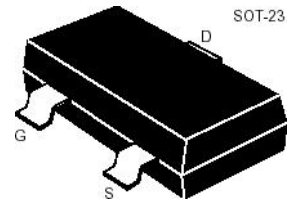
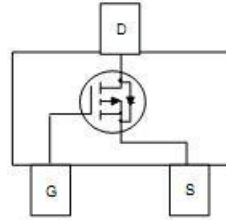


## FSS2301M

SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



**P-Channel Enhancement-Mode MOS FETs**

**P 沟道增强型 MOS 场效应管**

### ■ MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	$BV_{DSS}$	-20	V
Gate- Source Voltage 柵極-源極電壓	$V_{GS}$	$\pm 10$	V
Drain Current (continuous) 漏極電流-連續	$I_D$	-2.8	A
Drain Current (pulsed) 漏極電流-脈沖	$I_{DM}$	-12	A
Total Device Dissipation 總耗散功率 $T_A=25^\circ\text{C}$ 環境溫度為 $25^\circ\text{C}$	$P_D$	1000	mW
Junction 結溫	$T_J$	150	$^\circ\text{C}$
Storage Temperature 儲存溫度	$T_{stg}$	-55to+150	$^\circ\text{C}$

### ■ DEVICE MARKING 打標

**FSS2301M=A1SHB**



## FSS2301M

### ■ ELECTRICAL CHARACTERISTICS 電特性

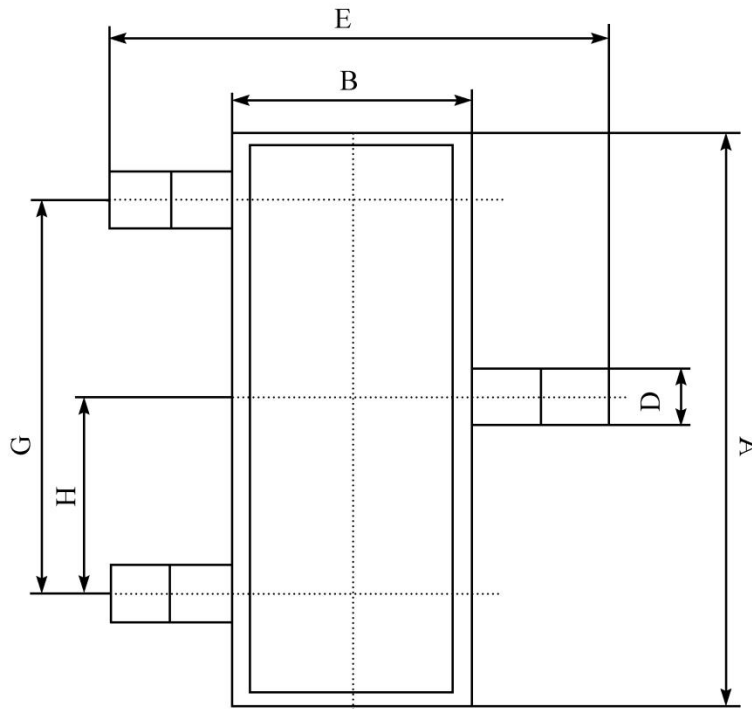
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如無特殊說明, 溫度為  $25^{\circ}\text{C}$ )

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓( $I_D = -250\mu\text{A}, V_{GS}=0\text{V}$ )	$BV_{DSS}$	-20	-22	—	V
Gate Threshold Voltage 柵極開啓電壓( $I_D = -250\mu\text{A}, V_{GS} = V_{DS}$ )	$V_{GS(th)}$	-0.5	-0.7	-1.5	V
Diode Forward Voltage Drop 內附二極管正向壓降( $I_S = -0.75\text{A}, V_{GS}=0\text{V}$ )	$V_{SD}$	—	—	-1.5	V
Zero Gate Voltage Drain Current 零柵壓漏極電流( $V_{GS}=0\text{V}, V_{DS} = -16\text{V}$ ) ( $V_{GS}=0\text{V}, V_{DS} = -16\text{V}, T_A=55^{\circ}\text{C}$ )	$I_{DSS}$	—	—	-1 -10	$\mu\text{A}$
Gate Body Leakage 柵極漏電流( $V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$ )	$I_{GSS}$	—	—	$\pm 100$	nA
Static Drain-Source On-State Resistance 靜態漏源導通電阻( $I_D = -2.7\text{A}, V_{GS} = -4.5\text{V}$ )	$R_{DS(ON)}$	—	90	110	$\text{m}\Omega$
Static Drain-Source On-State Resistance 靜態漏源導通電阻( $I_D = -2\text{A}, V_{GS} = -2.5\text{V}$ )	$R_{DS(ON)}$	—	110	150	$\text{m}\Omega$
Input Capacitance 輸入電容 ( $V_{GS}=0\text{V}, V_{DS} = -10\text{V}, f=1\text{MHz}$ )	$C_{ISS}$	—	200	—	pF
Output Capacitance 輸出電容 ( $V_{GS}=0\text{V}, V_{DS} = -10\text{V}, f=1\text{MHz}$ )	$C_{OSS}$	—	80	—	pF
Turn-ON Time 開啓時間 ( $V_{DS} = -10\text{V}, I_D = -2.7\text{A}, R_{GEN}=6\Omega$ )	$t_{(on)}$	—	8	—	ns
Turn-OFF Time 關斷時間 ( $V_{DS} = -10\text{V}, I_D = -2.7\text{A}, R_{GEN}=6\Omega$ )	$t_{(off)}$	—	60	—	ns

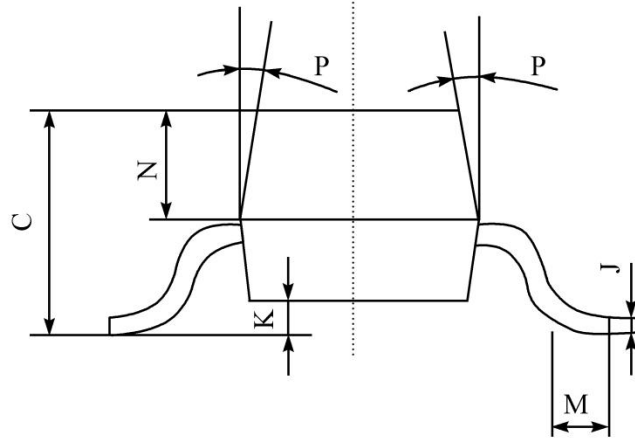
Pulse Width  $\leq 300 \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$

## FSS2301M

■ **DIMENSION** 外形封裝尺寸  
單位(UNIT): mm



序號	數值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [FOSAN](#) manufacturer:*

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [AOD464](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#)  
[405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#) [BSC884N03MS G](#) [BSF024N03LT3 G](#)  
[PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-](#)  
[7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#)  
[SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [STU5N65M6](#)  
[C3M0021120D](#) [DMN13M9UCA6-7](#) [BSS340NWH6327XTSA1](#) [MCM3400A-TP](#) [DMTH10H4M6SPS-13](#) [IRF40SC240ARMA1](#)  
[IPS60R1K0PFD7SAKMA1](#)